FAIRCHILD
SEMICONDUCTOR®

August 2007

FGPF30N30T
300V, 30A PDP Trench IGBT

Features

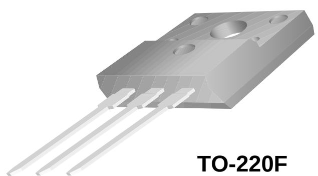
- High current capability
- Low saturation voltage: $V_{CE(sat)}$ =1.4V @ I_C = 20A
- High input impedance
- Fast switching
- RoHS complaint

Applications

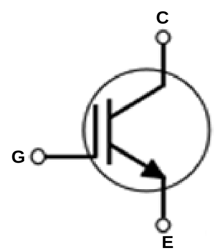
- PDP System

General Description

Using Novel Trench IGBT Technology, Fairchild's new series of trench IGBTs offer the optimum performance for PDP applications where low conduction and switching losses are essential.



1.Gate 2.Collector 3.Emitter



Absolute Maximum Ratings

Symbol	Description		Ratings	Units
V_{CES}	Collector to Emitter Voltage		300	V
V_{GES}	Gate to Emitter Voltage		± 30	V
$I_{C\ pulse\ (1)}$	Pulsed Collector Current	@ T_C = 25^{o}C	80	A
P_D	Maximum Power Dissipation	@ T_C = 25^{o}C	44.6	W
	Maximum Power Dissipation	@ T_C = 100^{o}C	17.8	W
T_J	Operating Junction Temperature		-55 to +150	^{o}C
T_{stg}	Storage Temperature Range		-55 to +150	^{o}C
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	^{o}C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$(IGBT)	Thermal Resistance, Junction to Case	-	2.8	^{o}C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	62.5	^{o}C/W

Notes :

(1) Repetitive tese, Pulse width = 100usec, Duty = 0.1

*I_C_pluse limited by max Tj

Package Marking and Ordering Information

Device Marking	Device	Package	Packaging Type	Qty per Tube	Max Qty per Box
FGPF30N30T	FGPF30N30TTU	TO-220F	Rail / Tube	50ea	-

Electrical Characteristics of the IGBT
T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector to Emitter Breakdown Voltage	V_{GE} = 0V, I_C = 250μA	300	-	-	V
$\Delta BV_{CES}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	V_{GE} = 0V, I_C = 250μA	-	0.26	-	V/°C
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}$, V_{GE} = 0V	-	-	100	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}$, V_{CE} = 0V	-	-	±400	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	I_C = 250μA, $V_{CE} = V_{GE}$	3.0	4.5	5.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C = 10A, V_{GE} = 15V	-	1.2	1.5	V
		I_C = 20A, V_{GE} = 15V	-	1.5	-	V
		I_C = 30A, V_{GE} = 15V, T_C = 25°C	-	1.7	-	V
		I_C = 30A, V_{GE} = 15V, T_C = 125°C	-	1.6	-	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE} = 30V, V_{GE} = 0V, f = 1MHz	-	1540	--	pF
C_{oes}	Output Capacitance		-	65	--	pF
C_{res}	Reverse Transfer Capacitance		-	55	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 200V, I_C = 20A, R_G = 20Ω, V_{GE} = 15V, Inductive Load, T_C = 25°C	-	22	--	ns
t_r	Rise Time		-	33	--	ns
$t_{d(off)}$	Turn-Off Delay Time		-	130	--	ns
t_f	Fall Time		-	180	300	ns
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 200V, I_C = 20A, R_G = 20Ω, V_{GE} = 15V, Inductive Load, T_C = 125°C	-	21	--	ns
t_r	Rise Time		-	34	--	ns
$t_{d(off)}$	Turn-Off Delay Time		-	140	--	ns
t_f	Fall Time		-	260	--	ns
Q_g	Total Gate Charge	V_{CE} = 200V, I_C = 20A, V_{GE} = 15V	-	65	--	nC
Q_{ge}	Gate to Emitter Charge		-	10	--	nC
Q_{gc}	Gate to Collector Charge		-	26	--	nC

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

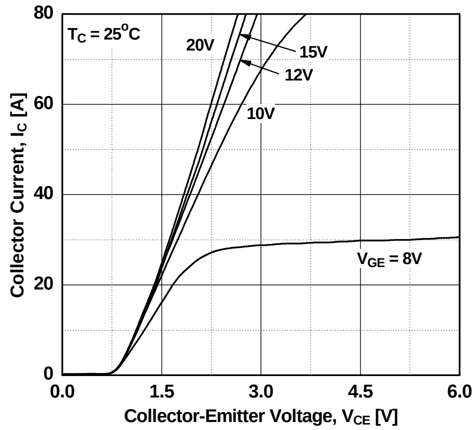


Figure 2. Typical Saturation Voltage Characteristics

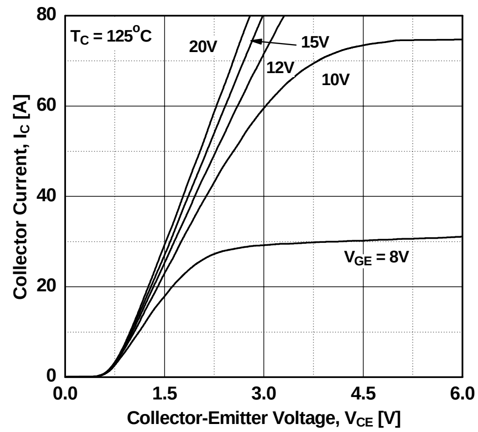


Figure 3. Typical Saturation Voltage Characteritics

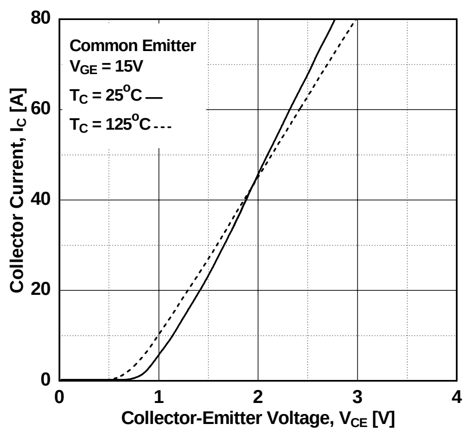


Figure 4. Transfer Characteristics

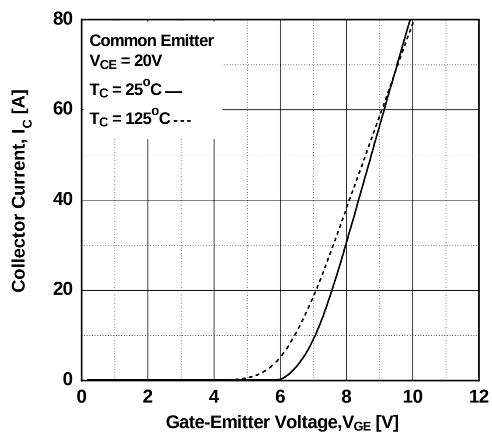


Figure 5. Saturation Voltage vs. Case

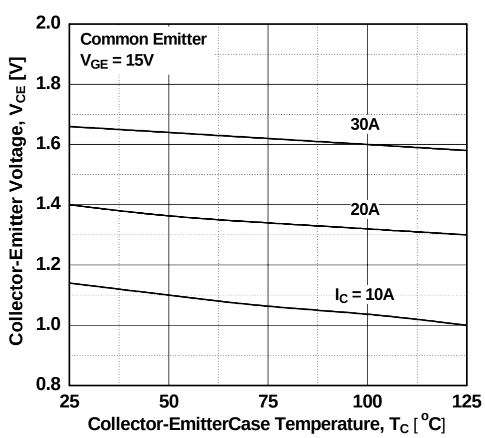
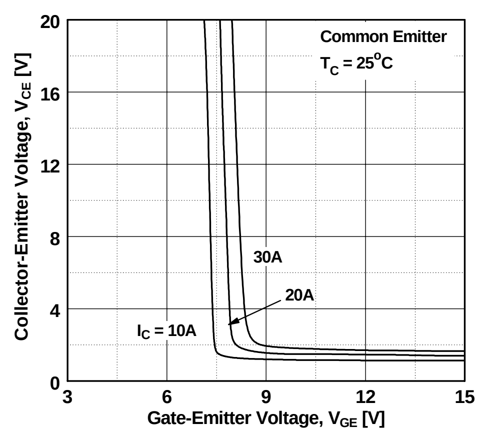


Figure 6. Saturation Voltage vs. Vge



Typical Performance Characteristics (Continued)

Figure 7. Saturation Voltage vs. Vge

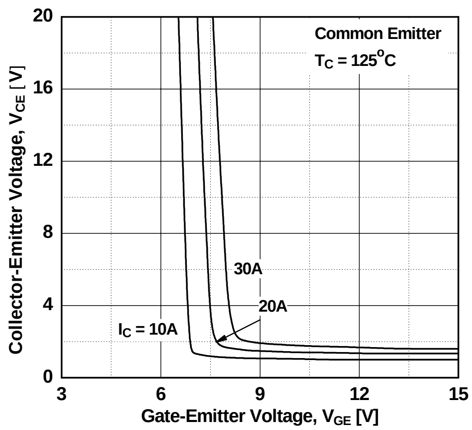


Figure 8. Capacitance Characteristics

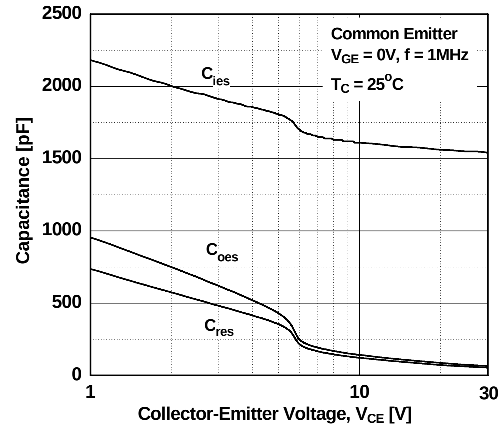


Figure 9. Gate Charge Characteristics

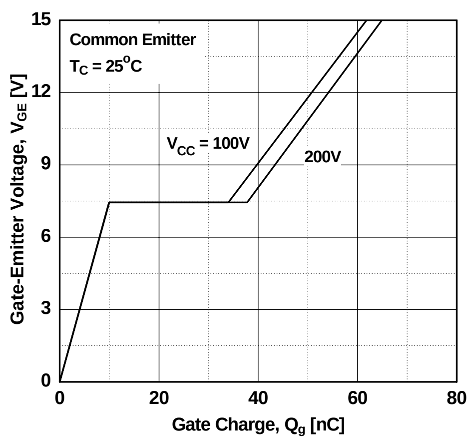


Figure 10. SOA Characteristics

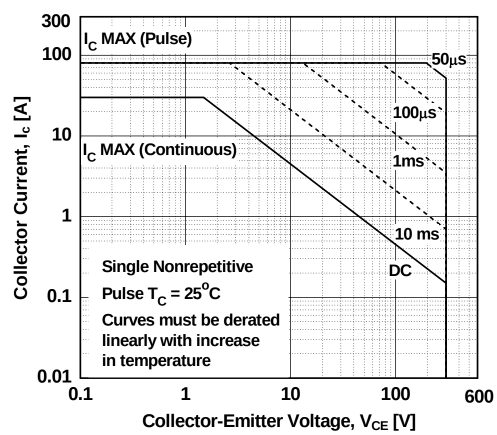


Figure 11. Turn-On Characteristics vs. Gate Resistance

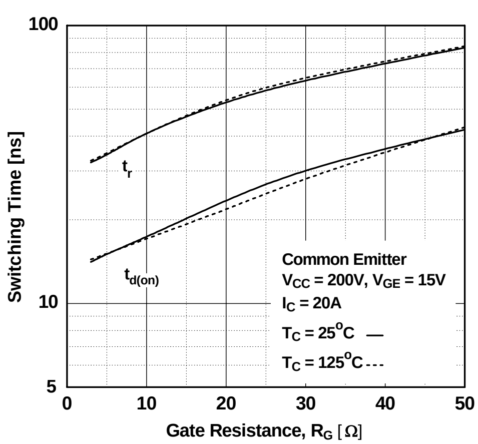
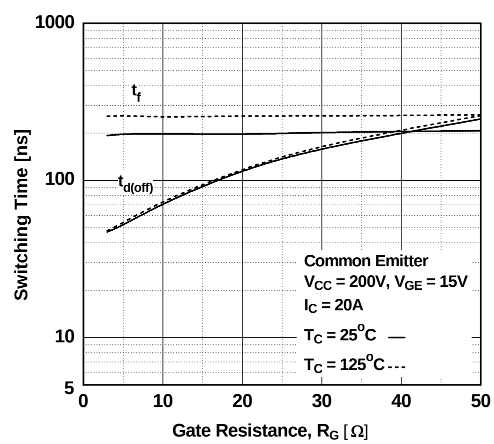


Figure 12. Turn-Off Characteristics vs. Gate Resistance



Typical Performance Characteristics (Continued)

Figure 13. Turn-On Characteristics vs. Collector Current

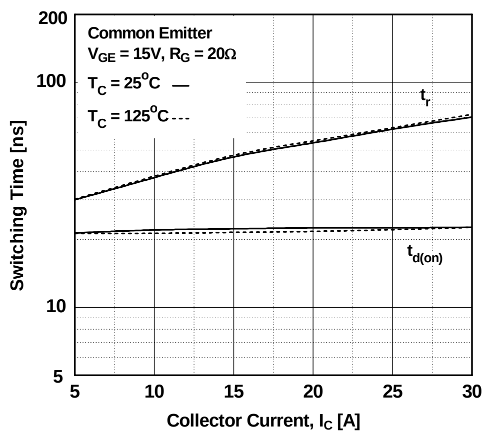


Figure 14. Turn-Off Characteristics vs. Collector Current

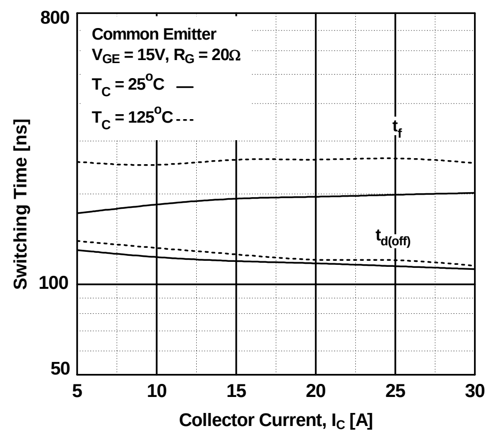


Figure 15. Switching Loss vs Gate Resistance

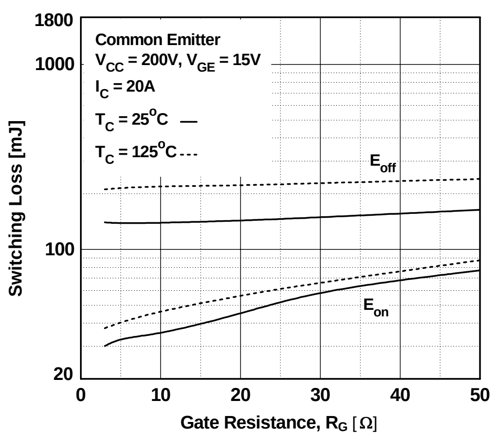


Figure 16. Switching Loss vs Collector Current

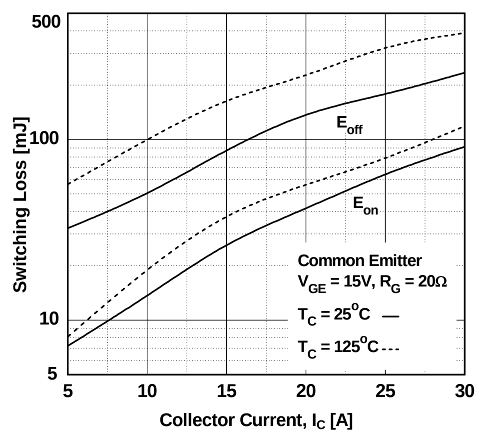
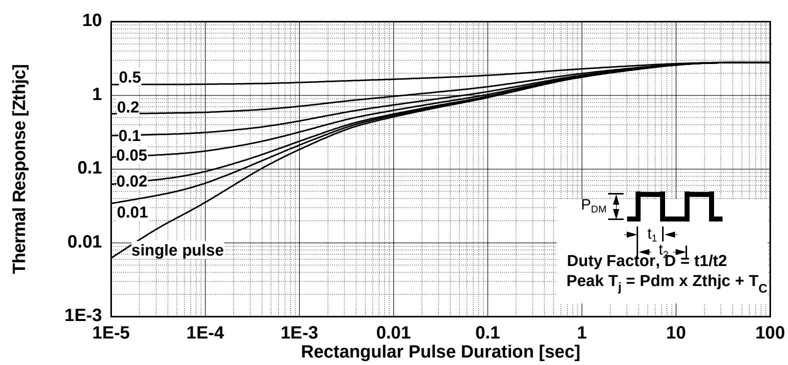
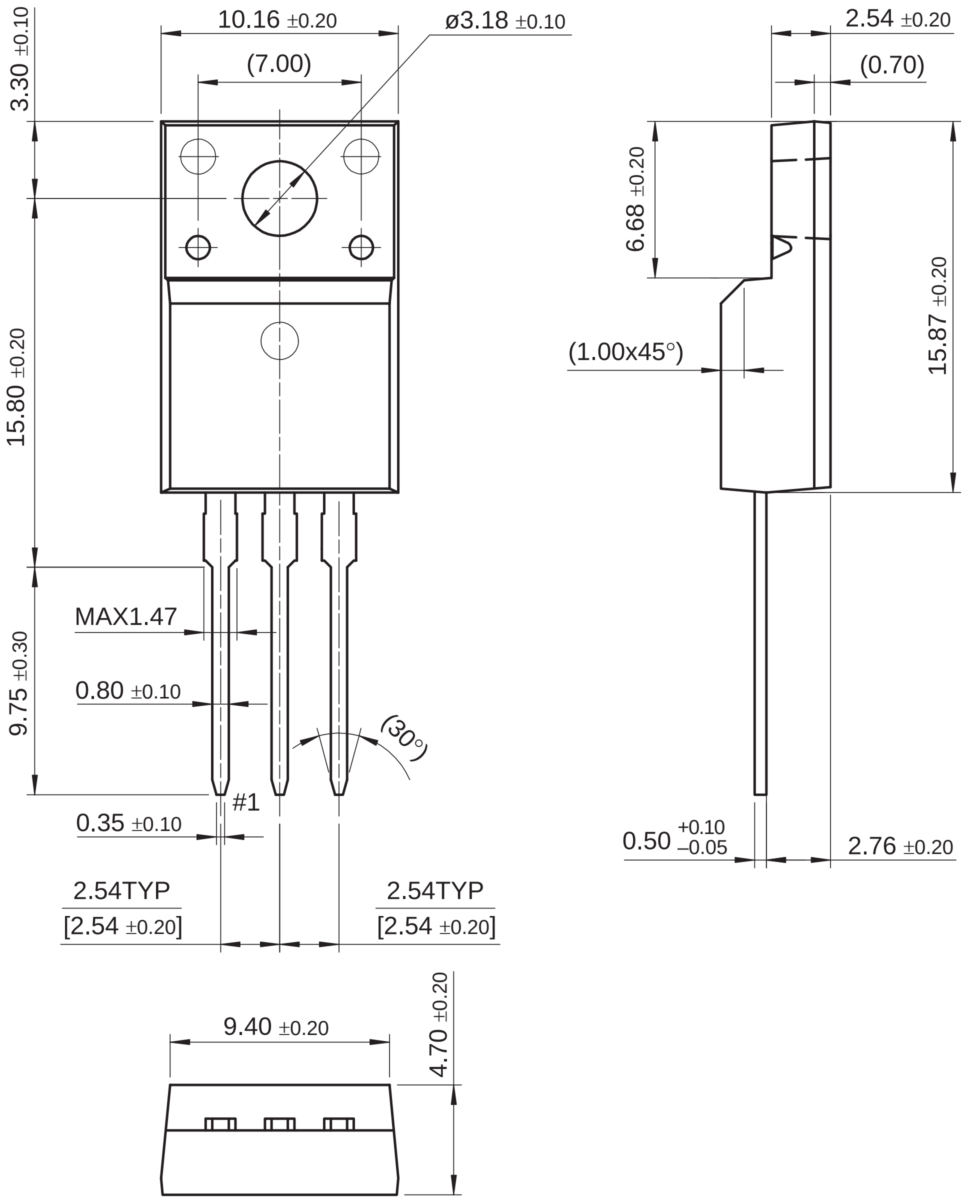


Figure 18. Transient Thermal Impedance of IGBT



Mechanical Dimensions

TO-220F



Dimensions in Millimeters

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